

In the Claims:

1. (Previously Presented) A polishing pad useful for planarizing a surface of a semiconductor device or a precursor thereto, the pad comprising:  
a polishing layer for planarizing the surface, the polishing layer having:
  - i. a hardness of about 40-70 Shore D;
  - ii. a tensile Modulus of about 150 -- 2,000 MPa at 40°C;
  - iii. a KEL of about 100-1,000 (1/Pa at 40°C); and
  - iv. an E' ratio at 30°C-90°C of about 1-4.6.
2. (Cancelled).
3. (Cancelled).
4. (Cancelled).
5. (Previously Presented) The polishing pad in accordance with Claim 1, wherein the polishing layer comprises a thermoplastic polymer.
6. (Previously Presented) The polishing pad in accordance with Claim 1, wherein the polishing layer comprises a thermoset polymer.
7. (Previously Presented) The polishing pad in accordance with Claim 1, wherein the polishing layer is non-porous.
8. (Previously Presented) The polishing pad in accordance with Claim 1, wherein the polishing layer is porous.
9. (Previously Presented) The polishing pad in accordance with Claim 1, wherein the polishing layer comprises a filler.

10. (Previously Presented) The polishing pad in accordance with Claim 1, wherein the polishing layer is devoid of a filler.
11. (Cancelled).
12. (Previously Presented) The polishing pad in accordance with Claim 1, wherein the polishing layer has a surface roughness of from about one to about nine micron Ra.
13. (Previously Presented) The polishing pad in accordance with Claim 1, wherein the pad has a belt configuration and the polishing layer comprises a thermoplastic polyurethane.
14. (Previously Presented) The polishing pad in accordance with Claim 1, wherein the pad has a molded belt configuration.
15. (Previously Presented) The polishing pad in accordance with Claim 1, wherein the pad comprises abrasive particles.
16. (Previously Presented) The polishing pad in accordance with Claim 1, wherein the pad is devoid of abrasive particles.
17. (Cancelled).
18. (Currently Amended) The polishing pad in accordance with Claim 1, wherein a polishing surface of the pad has a surface roughness of about 1 to about 9 microns Ra and the ratio of E' at 30°C to 90°C is from about 1 to about ~~3-63.5~~ 3-63.5.
19. (Previously Presented) The polishing pad in accordance with claim 1, wherein the polishing layer has a K<sub>EL</sub> in the range of about 125-850 (1/Pa at 40°C).

20. (Previously Presented) The polishing pad in accordance with claim 1, wherein the polishing layer has the following:
  - a surface roughness of 2-7 microns Ra,
  - hardness of about 45-65 Shore D,
  - tensile modulus of about 150 – 1,500 MPa at 40°C,
  - KEL of about 125-850 (1/Pa at 40°C), and
  - E' ratio at 30°C-90°C of about 1.0-4.0.
21. (Previously Presented) The polishing pad in accordance with claim 1, wherein the polishing layer has the following:
  - a surface roughness of 3-5 microns Ra,
  - hardness of about 55-63 Shore D,
  - tensile modulus of about 200 – 800 MPa at 40°C,
  - KEL of about 150-400 (1/Pa at 40°C), and
  - E' ratio at 30°C-90°C of about 1.0-3.5.
22. (Previously Presented) The polishing pad in accordance with Claim 1, wherein the polishing layer comprises a polyurethane.
23. (Previously Presented) The polishing pad in accordance with Claim 1, wherein the surface comprises a metal that comprises copper.
24. (Previously Presented) The polishing pad in accordance with Claim 1, wherein the surface comprises a metal that comprises tungsten.
25. (Previously Presented) The polishing pad in accordance with Claim 1, wherein the surface comprises a metal that comprises aluminum.
26. (Previously Presented) The polishing pad of claim 22, wherein the polyurethane is a polyether based polyurethane.

27. (Previously Presented) The polishing pad of claim 22, wherein the polyurethane is a polyester based polyurethane.

28 to 52 (Cancelled).